

A SnS2-based photomemristor driven by sun

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Abstract

We demonstrate experimentally that a sample of a SnS2 layered semiconductor compound with the area of 1 cm2 and the thickness of 100 μ m, contacted laterally by silver electrodes with the area of 1 mm2, acts naturally as a memristor device when illuminated by a sun simulator. Although the conductance of the device changes with the number of pulses or voltages sweeps, the current-voltage dependence is almost linear, showing only a very narrow but clearly pinched hysteresis, which is the main imprint of a memristor. This SnS2-based solid-state miniaturized photomemristor could be used for the implementation of all-optical neuromorphic circuits based on artificial neurons and synapses, oriented to learning algorithms of living organisms.